

ELECTRICALLY ERASABLE PROGRAMMABLE READ ONLY MEMORY (EEPROM) CELLS AND METHODS OF FABRICATING THE SAME

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ABSTRACT OF THE DISCLOSURE

Electrically erasable programmable read only memory (EEPROM) cells and methods of fabricating the same are provided. An EEPROM cell includes an isolation layer formed at a semiconductor substrate to define an active region. A source region, a buried N⁺ region and a drain region are serially disposed at the active region. A memory gate is
10 disposed to cross-over the buried N⁺ region. A first channel region is formed between the source region and the buried N⁺ region. A tunnel region is located between the buried N⁺ region and the memory gate and self-aligned with the buried N⁺ region.